

Title (en)
LPP EUV LIGHT SOURCE

Title (de)
LPP-EUV-LICHTQUELLE

Title (fr)
SOURCE DE RAYONNEMENT ULTRAVIOLET EXTREME A PLASMA CREE PAR LASER

Publication
EP 1730764 A2 20061213 (EN)

Application
EP 05724577 A 20050303

Priority
• US 2005007063 W 20050303
• US 80352604 A 20040317
• US 97991904 A 20041101

Abstract (en)
[origin: WO2005089131A2] An apparatus and method is described for effectively and efficiently providing plasma irradiation laser light pulses in an LPP EUV light source which may comprise a laser initial target irradiation pulse generating mechanism irradiating a plasma initiation target with an initial target irradiation pulse to form an EUV generating plasma having an emission region emitting in-band EUV light; a laser plasma irradiation pulse generating mechanism irradiating the plasma with a plasma irradiation pulse after the initial target irradiation pulse so as to compress emission material in the plasma toward the emission region of the plasma. The plasma irradiation pulse may comprise a laser pulse having a wavelength that is sufficiently longer than a wavelength of the initial target irradiation pulse to have an associated lower critical density resulting in absorption occurring within the plasma in a region of the plasma defined by the wavelength of the plasma irradiation pulse sufficiently separated from an initial target irradiation site to achieve compression of the emission material, and the may compress the emission region. The laser plasma irradiation pulse may produce an aerial mass density in the ablating cloud of the plasma sufficient to confine the favorably emitting plasma for increased conversion efficiency. The deposition region for the plasma irradiation pulse may be removed enough from the initial target surface so as to insure compression of the favorably emitting plasma. A high conversion efficiency laser produced plasma extreme ultraviolet ("EUV") light source may comprise a laser initial target irradiation pulse generating mechanism irradiating a plasma initiation target with a target irradiation pulse to form an EUV generating plasma emitting in-band EUV light; a plasma tamper substantially surrounding the plasma to constrain the expansion of the plasma.

IPC 8 full level
H01J 35/20 (2006.01); **G03F 7/20** (2006.01); **H05G 2/00** (2006.01)

CPC (source: EP KR)
B82Y 10/00 (2013.01 - EP); **G01J 1/00** (2013.01 - KR); **G03F 7/20** (2013.01 - KR); **G03F 7/70033** (2013.01 - EP); **H01J 35/20** (2013.01 - KR); **H01J 65/04** (2013.01 - KR); **H05G 2/003** (2013.01 - EP); **H05G 2/005** (2013.01 - EP); **H05G 2/008** (2013.01 - EP); **H01S 3/0085** (2013.01 - EP); **H01S 3/0092** (2013.01 - EP); **H01S 3/1611** (2013.01 - EP); **H01S 3/1653** (2013.01 - EP); **H01S 3/2255** (2013.01 - EP); **H01S 3/2325** (2013.01 - EP); **H01S 3/2375** (2013.01 - EP); **H01S 3/2383** (2013.01 - EP)

Designated contracting state (EPC)
DE FR NL

Designated extension state (EPC)
AL BA HR LV MK YU

DOCDB simple family (publication)
WO 2005089131 A2 20050929; **WO 2005089131 A3 20060608**; EP 1730764 A2 20061213; EP 1730764 A4 20100818; JP 2007529903 A 20071025; KR 20060125905 A 20061206

DOCDB simple family (application)
US 2005007063 W 20050303; EP 05724577 A 20050303; JP 2007503940 A 20050303; KR 20067019063 A 20060915